



Integrated Device Technology, Inc.

HIGH-PERFORMANCE CMOS BUS INTERFACE LATCHES

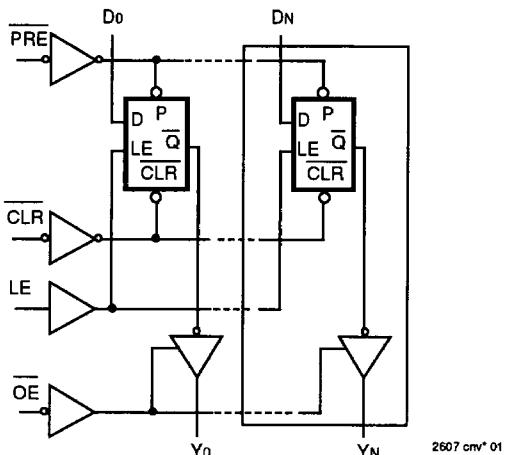
IDT54/74FCT841A/B/C
IDT54/74FCT843A/B/C
IDT54/74FCT844A/B/C
IDT54/74FCT845A/B/C

FEATURES:

- Equivalent to AMD's Am29841-46 bipolar registers in pinout/function, speed and output drive over full temperature and voltage supply extremes
- IDT54/74FCT841A/843A/844A/845A equivalent to FAST™ speed
- IDT54/74FCT841B/843B/844B/845B 25% faster than FAST**
- IDT54/74FCT841C/843C/844C/845C 40% faster than FAST**
- Buffered common latch enable, clear and preset inputs
- I_{OL} = 48mA (commercial) and 32mA (military)
- Clamp diodes on all inputs for ringing suppression
- CMOS power levels (1mW typ. static)
- TTL input and output level compatible
- CMOS output level compatible
- Substantially lower input current levels than AMD's bipolar Am29800 series (5μA max.)
- Product available in Radiation Tolerant and Radiation Enhanced versions
- Military product compliant to MIL-STD-883, Class B

FUNCTIONAL BLOCK DIAGRAM

IDT54/74FCT841/843/845



CEMOS is a trademark of Integrated Device Technology, Inc.
FAST is a trademark of National Semiconductor Co.

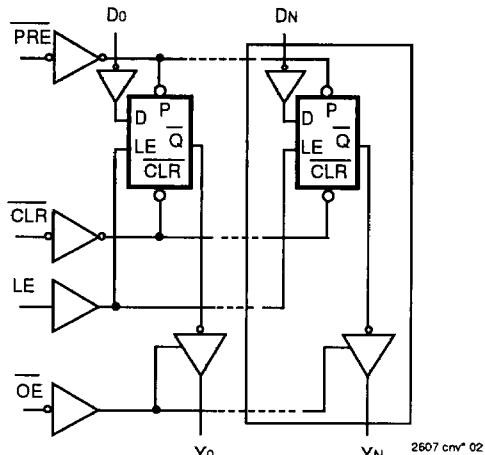
DESCRIPTION:

The IDT54/74FCT800 series is built using advanced CEMOS™, a dual metal CMOS technology.

The IDT54/74FCT840 series bus interface latches are designed to eliminate the extra packages required to buffer existing latches and provide extra data width for wider address/data paths or buses carrying parity. The IDT54/74FCT841 is a buffered, 10-bit wide version of the popular '373 function. The IDT54/74FCT843 and IDT54/74FCT844 are 9-bit wide buffered latches with Preset (PRE) and Clear (CLR)—ideal for parity bus interfacing in high-performance systems. The IDT54/74FCT845 is an 8-bit buffered latch with all the '843/4 controls, plus multiple enables (OE₁, OE₂, OE₃) to allow multiuser control of the interface, e.g., CS, DMA and RD/WR. It is ideal for use as an output port requiring high I_{OL}/I_{OH}.

All of the IDT54/74FCT800 high-performance interface family are designed for high-capacitance load drive capability, while providing low-capacitance bus loading at both inputs and outputs. All inputs have clamp diodes and all outputs are designed for low-capacitance bus loading in the high-impedance state.

IDT54/74FCT844



PRODUCT SELECTOR GUIDE

	Device		
	10-Bit	9-Bit	8-Bit
Non-Inverting	IDT54/74FCT841 A/B/C	IDT54/74FCT843 A/B/C	IDT54/74FCT845 A/B/C
Inverting		IDT54/74FCT844 A/B/C	

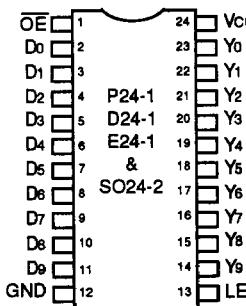
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MILITARY AND COMMERCIAL TEMPERATURE RANGES

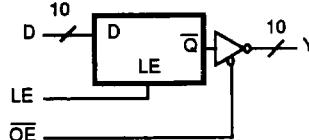
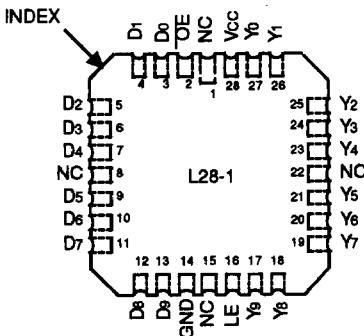
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PIN CONFIGURATIONS

IDT54/74FCT841 10-BIT LATCH

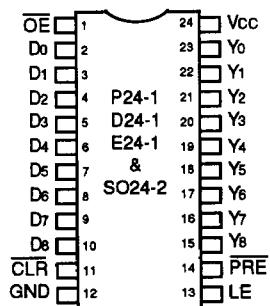


DIP/CERPACK/SOIC
TOP VIEW

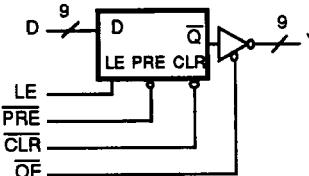
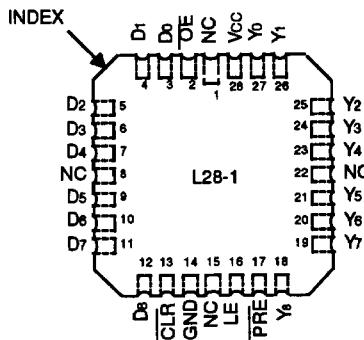


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IDT54/74FCT843/844 9-BIT LATCHES



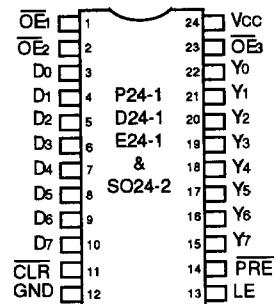
DIP/CERPACK/SOIC
TOP VIEW



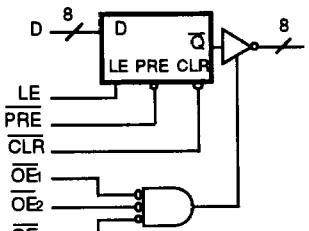
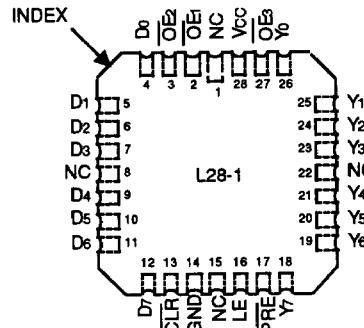
2607 cm* 06,07,08

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IDT54/74FCT845 8-BIT LATCH



DIP/CERPACK/SOIC
TOP VIEW



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PIN DESCRIPTION

Name	I/O	Description
IDT54/74FCT841/843/845 (Non-Inverting)		
CLR	I	When CLR is low, the outputs are LOW if OE is LOW. When CLR is HIGH, data can be entered into the latch.
DI	I	The latch data inputs.
LE	I	The latch enable input. The latches are transparent when LE is HIGH. Input data is latched on the HIGH-to-LOW transition.
YI	O	The 3-state latch outputs.
OE	I	The output enable control. When OE is LOW, the outputs are enabled. When OE is HIGH, the outputs (YI) are in the high-impedance (off) state.
PRE	I	Preset line. When PRE is LOW, the outputs are HIGH if OE is LOW. Preset overrides CLR.
IDT54/74FCT844 (Inverting)		
CLR	I	When CLR is low, the outputs are LOW if OE is LOW. When CLR is HIGH, data can be entered into the latch.
DI	I	The latch inverting data inputs.
LE	I	The latch enable input. The latches are transparent when LE is HIGH. Input data is latched on the HIGH-to-LOW transition.
YI	O	The 3-state latch outputs.
OE	I	The output enable control. When OE is LOW, the outputs are enabled. When OE is HIGH, the outputs (YI) are in the high-impedance (off) state.
PRE	I	Preset line. When PRE is LOW, the outputs are HIGH if OE is LOW. Preset overrides CLR.

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FUNCTION TABLE⁽¹⁾**IDT54/74FCT841/843/845**

Inputs					Internal	Outputs	Function
CLR	PRE	OE	LE	DI	QI	YI	
H	H	H	X	X	X	Z	High Z
H	H	H	H	L	L	Z	High Z
H	H	H	H	H	H	Z	High Z
H	H	H	L	X	NC	Z	Latched (High Z)
H	H	L	H	L	L	L	Transparent
H	H	L	H	H	H	H	Transparent
H	H	L	L	X	NC	NC	Latched
H	L	L	X	X	H	H	Preset
L	H	L	X	X	L	L	Clear
L	L	L	X	X	H	H	Preset
L	H	H	L	X	L	Z	Latched (High Z)
H	L	H	L	X	H	Z	Latched (High Z)

NOTE:

1. H = HIGH, L = LOW, X = Don't Care, NC = No Change,
Z = High Impedance

2607tbl03

FUNCTION TABLE⁽¹⁾**IDT54/74FCT844**

Inputs					Internal	Outputs	Function
CLR	PRE	OE	LE	DI	QI	YI	
H	H	H	X	X	X	Z	High Z
H	H	H	H	H	L	Z	High Z
H	H	H	H	L	H	Z	High Z
H	H	H	L	X	NC	Z	Latched (High Z)
H	H	L	H	H	L	L	Transparent
H	H	L	H	L	H	H	Transparent
H	H	L	L	X	NC	NC	Latched
H	L	L	X	X	H	H	Preset
L	H	L	X	X	L	L	Clear
L	L	L	X	X	H	H	Preset
L	H	H	L	X	L	Z	Latched (High Z)
H	L	H	L	X	H	Z	Latched (High Z)

NOTE:

1. H = HIGH, L = LOW, X = Don't Care, NC = No Change,
Z = High Impedance

2607tbl04

ABSOLUTE MAXIMUM RATINGS⁽¹⁾

Symbol	Rating	Commercial	Military	Unit
VTERM ⁽²⁾	Terminal Voltage with Respect to GND	-0.5 to +7.0	-0.5 to +7.0	V
VTERM ⁽³⁾	Terminal Voltage with Respect to GND	-0.5 to Vcc	-0.5 to Vcc	V
TA	Operating Temperature	0 to +70	-55 to +125	°C
TBIAS	Temperature Under Bias	-55 to +125	-65 to +135	°C
TSTG	Storage Temperature	-55 to +125	-65 to +150	°C
PT	Power Dissipation	0.5	0.5	W
IOUT	DC Output Current	120	120	mA

NOTE:

1. Stresses greater than those listed under ABSOLUTE MAXIMUM RATINGS may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability. No terminal voltage may exceed Vcc by +0.5V unless otherwise noted.

2. Input and Vcc terminals only.

3. Outputs and I/O terminals only.

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2607tbl06

CAPACITANCE (TA = +25°C, f = 1.0MHz)

Symbol	Parameter ⁽¹⁾	Conditions	Typ.	Max.	Unit
CIN	Input Capacitance	VIN = 0V	6	10	pF
COUT	Output Capacitance	VOUT = 0V	8	12	pF

NOTE:

1. This parameter is measured at characterization but not tested.

DC ELECTRICAL CHARACTERISTICS OVER OPERATING RANGE

Following Conditions Apply Unless Otherwise Specified: VLC = 0.2V; VHC = Vcc - 0.2V

Commercial: TA = 0°C to +70°C, Vcc = 5.0V ± 5%; Military: TA = -55°C to +125°C, Vcc = 5.0V ± 10%

Symbol	Parameter	Test Conditions ⁽¹⁾		Min.	Typ. ⁽²⁾	Max.	Unit
VIH	Input HIGH Level	Guaranteed Logic HIGH Level		2.0	—	—	V
VIL	Input LOW Level	Guaranteed Logic LOW Level		—	—	0.8	V
I _{IH}	Input HIGH Current	Vcc = Max.	V _I = Vcc	—	—	5	μA
I _{IL}	Input LOW Current		V _I = 2.7V	—	—	5 ⁽⁴⁾	
			V _I = 0.5V	—	—	-5 ⁽⁴⁾	
			V _I = GND	—	—	-5	
I _{OZH}	Off State (High Impedance) Output Current	Vcc = Max.	V _O = Vcc	—	—	10	μA
I _{OZL}			V _O = 2.7V	—	—	10 ⁽⁴⁾	
			V _O = 0.5V	—	—	-10 ⁽⁴⁾	
			V _O = GND	—	—	-10	
V _{IK}	Clamp Diode Voltage	Vcc = Min., IN = -18mA		—	-0.7	-1.2	V
I _{OS}	Short Circuit Current	Vcc = Max. ⁽³⁾ , V _O = GND		-75	-120	—	mA
V _{OH}	Output HIGH Voltage	Vcc = 3V, VIN = VLC or VHC, IOH = -32μA		V _{HC}	Vcc	—	V
		Vcc = Min. IOH = -300μA		V _{HC}	Vcc	—	
		VIN = VIH or VIL IOH = -15mA MIL.		2.4	4.3	—	
		IOH = -24mA COM'L.		2.4	4.3	—	
V _{OL}	Output LOW Voltage	Vcc = 3V, VIN = VLC or VHC, IOL = 300μA		—	GND	VLC	V
		Vcc = Min. IOL = 300μA		—	GND	VLC ⁽⁴⁾	
		VIN = VIH or VIL IOL = 32mA MIL.		—	0.3	0.5	
		IOL = 48mA COM'L.		—	0.3	0.5	

NOTES:

- For conditions shown as Max. or Min., use appropriate value specified under Electrical Characteristics for the applicable device type.
- Typical values are at Vcc = 5.0V, +25°C ambient and maximum loading.
- Not more than one output should be shorted at one time. Duration of the short circuit test should not exceed one second.
- This parameter is guaranteed but not tested.

2607tbl07

POWER SUPPLY CHARACTERISTICS

VLC = 0.2V; VHC = Vcc - 0.2V

Symbol	Parameter	Test Conditions ⁽¹⁾		Min.	Typ. ⁽²⁾	Max.	Unit
I _{CC}	Quiescent Power Supply Current	Vcc = Max. VIN ≥ VHC; VIN ≤ VLC		—	0.2	1.5	mA
ΔI _{CC}	Quiescent Power Supply Current TTL Inputs HIGH	Vcc = Max. VIN = 3.4V ⁽³⁾		—	0.5	2.0	mA
I _{CCD}	Dynamic Power Supply Current ⁽⁴⁾	Vcc = Max. Outputs Open OE = GND LE = Vcc One Input Toggling 50% Duty Cycle	VIN ≥ VHC VIN ≤ VLC	—	0.15	0.25	mA/ MHz
I _C	Total Power Supply Current ⁽⁶⁾	Vcc = Max. Outputs Open f _i = 10MHz 50% Duty Cycle	VIN ≥ VHC VIN ≤ VLC (FCT)	—	1.7	4.0	mA
		OE = GND LE = Vcc One Bit Toggling	VIN = 3.4V VIN = GND	—	2.0	5.0	
		Vcc = Max. Outputs Open f _i = 2.5MHz 50% Duty Cycle	VIN ≥ VHC VIN ≤ VLC (FCT)	—	3.2	6.5 ⁽⁵⁾	
		OE = GND LE = Vcc Eight Bits Toggling	VIN = 3.4V VIN = GND	—	5.2	14.5 ⁽⁵⁾	

NOTES:

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1. For conditions shown as Max. or Min., use appropriate value specified under Electrical Characteristics for the applicable device type.

2. Typical values are at Vcc = 5.0V, +25°C ambient.

3. Per TTL driven input (VIN = 3.4V); all other inputs at Vcc or GND.

4. This parameter is not directly testable, but is derived for use in Total Power Supply calculations.

5. Values for these conditions are examples of the I_{CC} formula. These limits are guaranteed but not tested.6. I_C = I_{QUIESCENT} + I_{INPUTS} + I_{DYNAMIC}

I_C = I_{CC} + ΔI_{CC} D_HN_T + I_{CCD} (f_C/2 + f_iN_i)

I_{CC} = Quiescent CurrentΔI_{CC} = Power Supply Current for a TTL High Input (VIN = 3.4V)D_H = Duty Cycle for TTL Inputs HighN_T = Number of TTL Inputs at DHI_{CCD} = Dynamic Current Caused by an Input Transition Pair (HLH or LHL)f_C = Clock Frequency for Register Devices (Zero for Non-Register Devices)f_i = Input FrequencyN_i = Number of Inputs at f_i

All currents are in millamps and all frequencies are in megahertz.

SWITCHING CHARACTERISTICS OVER OPERATING RANGE

Symbol	Parameter	Conditions ⁽¹⁾	FCT841A/843A- 844A/845A				FCT841B/843B- 844B/845B				FCT841C/843C- 844C/845C				Unit	
			Com'l.		Mil.		Com'l.		Mil.		Com'l.		Mil.			
			Min. ⁽²⁾	Max.	Min. ⁽²⁾	Max.	Min. ⁽²⁾	Max.	Min. ⁽²⁾	Max.	Min. ⁽²⁾	Max.	Min. ⁽²⁾	Max.		
(FCT841, 843, 845)	Propagation Delay Di to Yi (LE = HIGH)	CL = 50pF	1.5	9.0	1.5	10.0	1.5	6.5	1.5	7.5	1.5	5.5	1.5	6.3	ns	
		RL = 500Ω														
tPLH tPHL	(FCT844)	CL = 300pF ⁽⁴⁾	1.5	13.0	1.5	15.0	1.5	13.0	1.5	15.0	1.5	13.0	1.5	15.0	ns	
		RL = 500Ω														
tPLH tPHL	Propagation Delay Di to Yi (LE = HIGH)	CL = 50pF	1.5	10.0	1.5	12.0	1.5	8.0	1.5	9.0	1.5	7.0	1.5	8.0	ns	
		RL = 500Ω														
tPLH tPHL	Propagation Delay LE to Yi	CL = 50pF	1.5	12.0	1.5	13.0	1.5	8.0	1.5	10.5	1.5	6.4	1.5	6.8	ns	
		RL = 500Ω														
tPLH tPHL	Propagation Delay, PRE to Yi	CL = 50pF	1.5	12.0	1.5	14.0	1.5	8.0	1.5	10.0	1.5	7.0	1.5	9.0	ns	
		RL = 500Ω	1.5	14.0	1.5	17.0	1.5	10.0	1.5	13.0	1.5	9.0	1.5	12.0		
tPHL tPLH	Propagation Delay, CLR to Yi	CL = 50pF	1.5	13.0	1.5	14.0	1.5	10.0	1.5	11.0	1.5	9.0	1.5	10.0	ns	
		RL = 500Ω	1.5	14.0	1.5	17.0	1.5	10.0	1.5	10.0	1.5	9.0	1.5	9.0		
tPZH tPZL	Output Enable Time OE to Yi	CL = 50pF	1.5	11.5	1.5	13.0	1.5	8.0	1.5	8.5	1.5	6.5	1.5	7.3	ns	
		RL = 500Ω														
tPHZ tPLZ	Output Disable Time OE to Yi	CL = 300pF ⁽⁴⁾	1.5	23.0	1.5	25.0	1.5	14.0	1.5	15.0	1.5	12.0	1.5	13.0	ns	
		RL = 500Ω														
tsu	Data to LE Set-up Time		CL = 5pF ⁽⁴⁾	1.5	7.0	1.5	9.0	1.5	6.0	1.5	6.5	1.5	5.7	1.5	6.0	ns
	Data to LE Hold Time		RL = 500Ω	2.5	—	2.5	—	2.5	—	2.5	—	2.5	—	2.5	—	
tw	LE Pulse Width ⁽³⁾		HIGH	2.5	—	3.0	—	2.5	—	2.5	—	2.5	—	2.5	—	ns
	PRE Pulse Width ⁽³⁾		LOW	4.0	—	5.0	—	4.0	—	4.0	—	4.0	—	4.0	—	
tw	CLR Pulse Width ⁽³⁾		LOW	5.0	—	7.0	—	4.0	—	4.0	—	4.0	—	4.0	—	ns
	RE Recovery Time PRE to LE			4.0	—	5.0	—	4.0	—	4.0	—	4.0	—	4.0	—	
tREM	RE Recovery Time CLR to LE			4.0	—	4.0	—	4.0	—	4.0	—	4.0	—	4.0	—	ns
	RE Recovery Time CLR to LE			3.0	—	3.0	—	3.0	—	3.0	—	3.0	—	3.0	—	

NOTES:

1. See test circuit and waveforms.
2. Minimum limits are guaranteed but not tested on Propagation Delays.
3. These parameters are guaranteed but not tested.
4. These conditions are guaranteed but not tested.

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